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PROGRAMMABILITY BASED UPON

TRANSISTOR GATE OXIDE BREAKDOWN

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:	JACK ZEZHONG PENG ET AL.	EXAMINER:				
APPLICATION NO.:	TO BE ASSIGNED	ART UNIT:				
FILED:	HEREWITH	CONF. NO:				
FOR: COMBINATION FIELD PROGRAMMABLE GATE ARRAY ALLOWING DYNAMIC BERROGRAMMABILITY AND NON-VOLATILE						

<u>Information Disclosure Statement Within Three Months of</u>
<u>Application Filing or Before First Action – 37 C.F.R. § 1.97(b)</u>

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

1. Timing of Submission

This information disclosure is being filed within three months of the filing date of this application or date of entry into the national stage of an international application or before the mailing date of a first Office action on the merits, whichever occurs last [37 C.F.R. § 1.97(b)]. The references listed on the enclosed Form PTO-1449 (modified) may be material to the examination of this application; the Examiner is requested to make them of record in the application.

2. <u>Cited Information</u>

Copies of the following references are enclose						
	All cited references References marked by asterisks The following: All Non-Patent References					

	Copies of the following references can be found in parent U.S. Application No. :							
	☐ All cited references☐ References marked by asterisks☐ The following:							
	This application was filed after 30 June 2003 and no copies of U.S. patents nor published applications are enclosed (See Notice of Deputy Commissioner Kunin on 11 July 2003).							
	The following references are not in English. For each such reference, the undersigned has enclosed (i) a translation of the reference; (ii) a copy of a communication from a foreign patent office or International Searching Authority citing the reference, (iii) a copy of a reference which appears to be an English-language counterpart, or (iv) an English-language abstract for the reference prepared by a third party. Applicant has not verified that the translation, English-language counterpart or third-party abstract is an accurate representation of the teachings of the non-English reference, though, and reserves the right to demonstrate otherwise.							
	 ☐ All cited references ☐ References marked by ampersands ☑ The following: JP61292295 							
<u>Effect</u>	Effect of Information Disclosure Statement (37 C.F.R. § 1.97(h))							
that: examinesult cited applicant to	This Information Disclosure Statement is not to be construed as a representation that: (i) a search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols results and the like reported by third parties are accurate or enabling; or (iv) the cited information is, or is considered to be, material to patentability. In addition applicant does not admit that any enclosed item of information constitutes prior art to the subject invention and specifically reserves the right to demonstrate that any such reference is not prior art.							
Fee P	<u>ayment</u>							
	No fees are believed due because this Information Disclosure Statement is being filed before the mailing date of the first Office Action.							
	Applicant further submits that no fee is due in light of the following certification under 37 C.F.R. § 1.97(e) (check only one):							
	In accordance with 37 C.F.R. § 1.97(e)(1), the undersigned hereby states that each item of information submitted herewith was cited in a communication from a foreign patent office in a counterpart							

3.

4.

foreign application not more than three months prior to the filing of this statement; or

In accordance with 37 C.F.R. § 1.97(e)(2), the undersigned hereby states that no item of information submitted herewith was cited in a communication from a foreign patent office in a counterpart foreign application, or, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c), more than three months prior to the filing of this statement.

However, should the Commissioner determine that fees are due in order for this Information Disclosure Statement to be considered, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 50-0665.

5. Patent Term Adjustment (37 C.F.R. § 1.704(d))

The undersigned states that each item of information submitted herewith was cited in a communication from a foreign patent office in a counterpart application and that this communication was not received by any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filing of this statement. 37 C.F.R. § 1.704(d).

Respectfully submitted, Perkins Coie LLP

Chun M. Ng

Registration No. 36,878

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Sheet

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4

	COMPLETE IF KNOWN	
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First Named Inventor	Jack Zezhong Peng	
Group Art Unit		
Examiner Name		
Attorney Docket No.	384848013US1	

				U.S. PATENT DOCUMENTS		
Examiner Initials*	Cite No.	U.S. Patent of	r Application Kind Code (if known)	Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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*EXAMINER:	Initial if reference considered, whether or not criteria is in conformar	nce with MPEP 609. Draw line through citation if not in conformance and not
	considered. Include copy of this form with next communication to a	pplication(s).

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2

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		OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS	
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